

# isc N-Channel MOSFET Transistor

### AOD4146

### FEATURES

- Drain Current –I\_D= 55A@ T\_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage-: V<sub>DSS</sub>=30V(Min)
- Static Drain-Source On-Resistance : R<sub>DS(on)</sub> =5.6m Ω (Max)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRIPTION

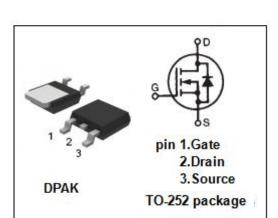
• Designed for use in switch mode power supplies and general purpose applications.

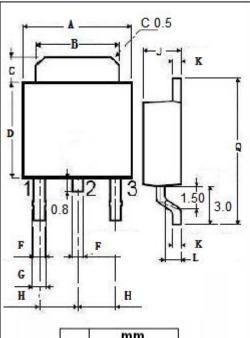
| ABSOLUTE MAXIMUM RATINGS(Ta=23.0) |  |         |      |  |  |  |
|-----------------------------------|--|---------|------|--|--|--|
| SYMBOL                            | PARAMETER                              | VALUE   | UNIT |  |  |  |
| V <sub>DSS</sub>                  | Drain-Source Voltage                   | 30      | V    |  |  |  |
| V <sub>GS</sub>                   | Gate-Source Voltage-Continuous         | ±20     | V    |  |  |  |
| ID                                | Drain Current-Continuous               | 55      | А    |  |  |  |
| I <sub>DM</sub>                   | Drain Current-Single Pluse             | 190     | А    |  |  |  |
| P <sub>D</sub>                    | Total Dissipation @T <sub>c</sub> =25℃ | 62      | W    |  |  |  |
| TJ                                | Max. Operating Junction Temperature    | -55~175 | °C   |  |  |  |
| T <sub>stg</sub>                  | Storage Temperature -55~175            |         | °C   |  |  |  |

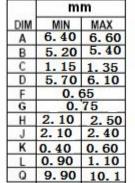
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

# <sup>1</sup> *isc & iscsemi* is registered trademark

SYMBOLPARAMETERMAXUNITRth j-cThermal Resistance, Junction to Case2.4°C/W







isc website: <u>www.iscsemi.com</u>

**THERMAL CHARACTERISTICS** 



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### **ELECTRICAL CHARACTERISTICS**

#### T<sub>c</sub>=25℃ unless otherwise specified

| SYMBOL              | PARAMETER                       | CONDITIONS   | MIN | МАХ        | UNIT       |
|---------------------|---------------------------------|--|-----|------------|------------|
| V(BR)DSS            | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 0.25mA   | 30  |            | V          |
| V <sub>GS(th)</sub> | Gate Threshold Voltage          | $V_{DS}$ = $V_{GS}$ ; $I_D$ = 0.25mA   | 1.6 | 3.0        | V          |
| R <sub>DS(on)</sub> | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> =20A<br>V <sub>GS</sub> = 10V; I <sub>D</sub> =20A@TJ=125℃           |     | 5.6<br>8.9 | mΩ         |
| lgss                | Gate-Body Leakage Current       | V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0   |     | ±100       | nA         |
| I <sub>DSS</sub>    | Zero Gate Voltage Drain Current | V <sub>DS</sub> =30V; V <sub>GS</sub> = 0<br>V <sub>DS</sub> =30V; V <sub>GS</sub> = 0@T <sub>J</sub> =55℃ |     | 100<br>500 | μ <b>Α</b> |
| V <sub>SD</sub>     | Forward On-Voltage              | I <sub>S</sub> = 1A; V <sub>GS</sub> = 0   |     | 1          | V          |



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